

### IEEE 802.3af/at-compliant PD Interface Controller

### **General Description**

The SY28902B is a power device (PD) controller with all the features needed to implement the IEEE802.3at/at protocol. It employs a high-power classification scheme, delivering 38.7W, 52.7W, 70W or 90W of power at the PD RJ45 connector. The SY28902B is fully compatible with IEEE 802.3af/at.

An internal charge-pump is used for enabling the use of external low  $R_{\text{DS(ON)}}$  N-channel MOSFETs and increase the end-to-end power transmission efficiency. The SY28902B includes an integrated signature resistor, under-voltage lockout, a power good output and thermal protection. The start-up inrush current can be adjusted using an external capacitor. Auxiliary power override is supported for voltages higher than 9V applied to the AUX pin.

802.3at, 802.3af and up to 90W power levels are all supported by configuring external components.

The SY28902B is available in a compact DFN3×3-10 package.

#### **Features**

- IEEE 802.3af/at Powered Device (PD) Controller
- Supports Up to 90W PDs
- Supports All of the Following Standards:
  - High Power Mode: 38.7W, 52.7W, 70W and 90W
  - IEEE 802.3at 25.5W Compliant
  - IEEE 802.3af up to 13W Compliant
- 100V Robust Surge Protection (Abs. Max.)
- Integrated Signature Resistor
- Thermal Shutdown Protection
- External Hot Swap N-Channel MOSFET for Lowest Power Dissipation and Highest System Efficiency
- Configurable Aux Power Support as Low as 9V
- -40°C to 125°CJunction Temperature Range

### **Applications**

- Security Cameras
- Base Stations
- IEEE 802.3bt Compliant Devices
- Video and VoIP Telephones

### **Typical Application**

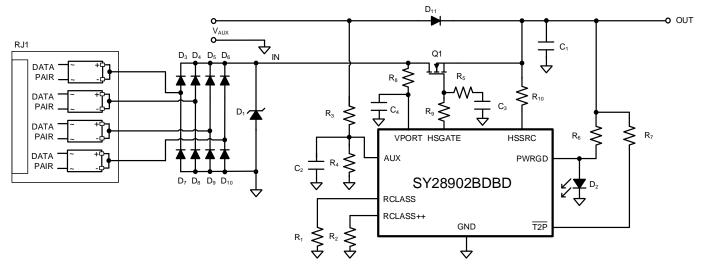


Figure 1. Schematic Diagram



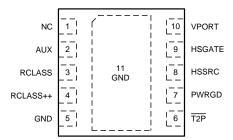


# **Ordering Information**

Ordering Part Number	Package Type	Top Mark
SY28902BDBD	DFN3×3-10 RoHS Compliant and Halogen Free	EEMxyz

x=year code, y=week code, z= lot number code

# Pinout (top view)



Pin Name	NO.	TYPE	Pin Description
GND	5, 11	-	Device ground. The exposed pad must be electrically and thermally connected to pin5 and PCB GND.
AUX	2	ı	Auxiliary sense pin. A resistive divider from the auxiliary power input to AUX sets the voltage at which the auxiliary supply takes over. In auxiliary power operation, HSGATE pulls down, the signature resistor disconnects, classification is disabled, and the PWRGD pin is high impedance and T2P indicates max available power. The
			AUX pin sinks I <sub>AUXH</sub> when below its threshold voltage of V <sub>AUXT</sub> to provide hysteresis.  Connect to GND when not used.
RCLASS	3	0	Configurable PoE classification resistor.
RCLASS++	4	0	Configurable PoE classification resistor.
T2P	6	0	PSE type indicator, open-drain output.
PWRGD	7	0	Power good indicator. Open-drain output. Pulls to GND during V <sub>CLASS</sub> and inrush.
HSSRC	8	I	External hot-swap MOSFET source. Connect to the source of the external MOSFET.
HSGATE	9	0	External hot-swap MOSFET gate control, output. Connect to the gate of the external MOSFET.
VPORT	10	I	PD interface upper power rail and external hot-swap MOSFET drain connection.
NC	1	-	No electrical connection internally. May connect to any potential.



# **Block Diagram**

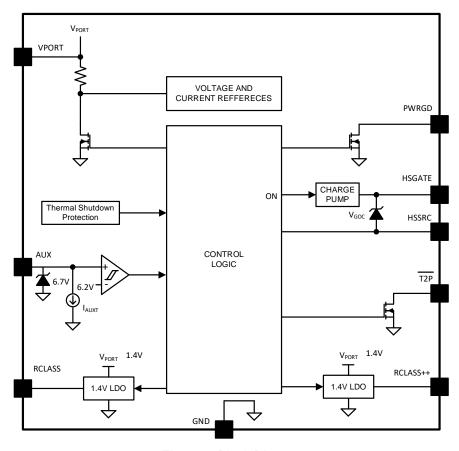


Figure 2. Block Diagram

# **Absolute Maximum Ratings**

Parameter (Note1) (Note4)	Min	Max	Unit
VPORT, HSSRC, HSGATE, T2P, PWRGD	-0.3	100	V
RCLASS, RCLASS++	-0.3	6 (and ≤ VPORT)	
HSGATE Current	-20	20	
AUX Current	-1.4	1.4	mΑ
T2P, PWRGD Current		5	
Junction Temperature, Operating	-40	125	
Lead Temperature (Soldering, 10sec.)		300	°C
Storage Temperature	-65	150	

# **Thermal Information**

Parameter (Note2)	Тур	Unit
θ <sub>JA</sub> Junction-to-ambient Thermal Resistance	60.5	°C \\\\
θ <sub>JC</sub> Junction-to-case Thermal Resistance	31	°C/W
P <sub>D</sub> Power Dissipation T <sub>A</sub> =25°C	1.65	W



# **Recommended Operating Conditions**

Parameter (Note5)	Min	Max	Unit
VPORT, HSSRC	0	60	\/
RCLASS, RCLASS++	0	5 (and ≤ VPORT)	V
Ambient Temperature	-40	125	°C

### **Electrical Characteristics**

(The specification in the following table applies over the  $-40^{\circ}\text{C} \le \text{T}_{\text{J}} \le +125^{\circ}\text{C}$ . Typical values are for  $\text{T}_{\text{A}} = 25^{\circ}\text{C}$ , unless otherwise noted.). (Note4)

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
VPORT Operating Input Voltage		At VPORT Pin			60	V
VPORT Signature Range	Vsig	At VPORT Pin	1.5		10	V
VPORT Classification Range	VCLASS	At VPORT Pin	12.5		21	V
VPORT Mark Range	VMARK	At VPORT Pin, Preceded by VcLASS	5.6		10	V
VPORT Aux Mode Range		At VPORT Pin, AUX > V <sub>AUXT</sub>	8		60	V
Signature/Class Hysteresis Window			1.0			V
Reset Threshold	V <sub>RESET</sub>	At VPORT Pin, Preceded by V <sub>CLASS</sub>	2.6		5.6	V
Hot Swap Turn-On Voltage	V <sub>HSON</sub>			35	37	V
Hot Swap Turn-Off Voltage	VHSOFF		30	31		V
Hot Swap On/Off Hysteresis Window			3			٧
Supply Current	•					
Supply Current		Vvport=Vhssrc=57V			1	mA
Supply Current During Classification		V <sub>VPORT</sub> = 17.5 V, RCLASS and RCLASS++ Open	0.1	0.2	0.5	mA
Supply Current During Mark Event		VVPORT=VMARK After 1st Classification Event	0.5		1.8	mA
<b>Detection and Classification Sig</b>	nature		•		•	
Detection Signature Resistance		V <sub>SIG</sub> (Note 3)	23.7	24.4	25.2	kΩ
Resistance During Mark Event		V <sub>MARK</sub> (Note 3)	5.8	8.3	11	kΩ
RCLASS/RCLASS++ Operating Voltage		-10mA ≥ I <sub>RCLASS</sub> ≥ -36mA, V <sub>CLASS</sub>	1.32	1.40	1.43	V
Classification Signature Stability Time		V <sub>VPORT</sub> Step to 17.5V, 34.8Ω from RCLASS or RCLASS++ to GND			2	ms
Analog/Digital Interface	1		•	l		
AUX Threshold	V <sub>AUXT</sub>		6.0	6.2	6.4	V
AUX Hysteresis	V <sub>AUX,HYS</sub>			0.4		V
AUX Pin Hysteresis Current	I <sub>AUXT</sub>	V <sub>AUX</sub> = 6.1V	0.8	2.1	4	μA
T2P Output Low		1mA Load			0.8	V
PWRGD Output Low		1mA Load			0.8	V
PWRGD Leakage Current		V <sub>PWRGD</sub> = 60V			5	μA
T2P Leakage Current		T2P = 60V			5	μA





Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Hot Swap Control	•					
HSGATE Pull-up Current	I <sub>GPU</sub>	V <sub>HSGATE</sub> - V <sub>HSSRC</sub> = 5V (Note 7)	-27	-22	-18	μA
HSGATE Open Circuit Voltage	V <sub>G</sub> OC	-10μA load, with Respect to HSSRC	10		17	V
HSGATE Pull-Down Current		V <sub>HSGATE</sub> - V <sub>HSSRC</sub> = 5V	200			μA
Timing						
T2P Frequency	f <sub>T2P</sub>	V <sub>AUX</sub> > V <sub>AUXT</sub> , and RCLASS++ has resistor to GND	690	840	990	Hz
T2P Duty Cycle in PoE Operation (Note 6)		After 3-Event Classification		50		%
T2P Duty Cycle in Auxiliary Supply Operation (Note 6)		V <sub>AUX</sub> > V <sub>AUXT</sub> , and RCLASS++ has resistor to GND at T <sub>A</sub> = 25°C.		50		%

**Note 1:** Stresses beyond the "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only. Functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specification are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**Note 2:**  $\theta_{JA}$  is measured in the natural convection at  $T_A = 25^{\circ}\text{C}$  on the Silergy EVB test board.

**Note 3:** Signature resistance specifications do not include resistance added by the external diode bridge, which can add as much as  $1.1k\Omega$  to the port resistance.

**Note 4:** All voltages with respect to GND unless otherwise noted. Positive currents flow into pins; negative currents flow out of pins unless otherwise noted.

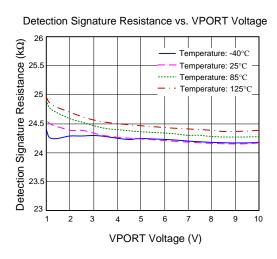
**Note 5:** This IC includes over-temperature protection that is intended to protect the device during momentary overload conditions. Junction temperature will exceed 150°C when over-temperature protection is active. Continuous operation above the specified maximum operating junction temperature may impair device reliability.

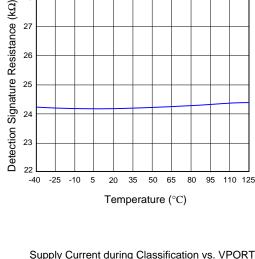
**Note 6:** Specified as the percentage of the period which  $\overline{T2P}$  is low impedance with respect to the GND.

Note 7:  $I_{GPU}$  available in PoE-powered operation. That is, available after  $V_{VPORT} > V_{HSON}$  and  $V_{AUXT}$ , over the range where  $V_{VPORT}$  is between  $V_{HSOFF}$  and 60V.



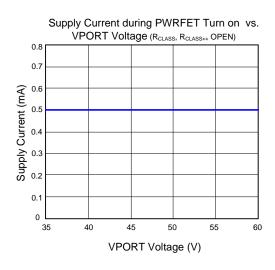
# **Typical Performance Characteristics**

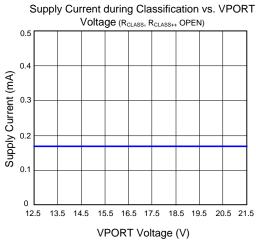


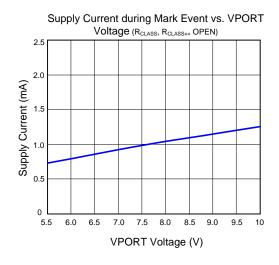


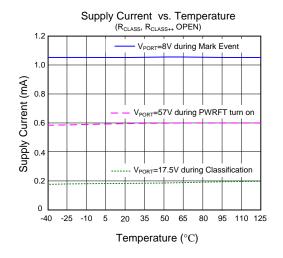
Detection Signature Resistance vs. Temperature

 $(V_{PORT}=8V, R_{CLASS}=49.9\Omega, R_{CLASS++}=118\Omega)$ 



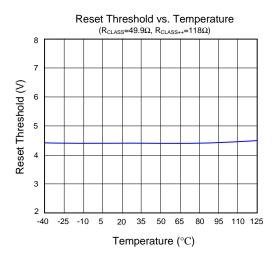


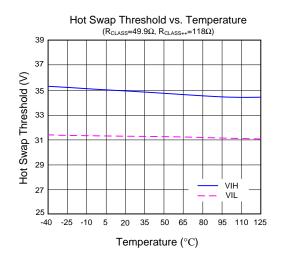


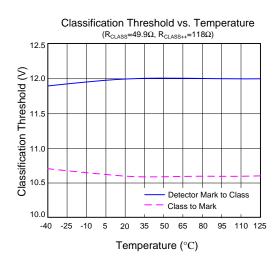


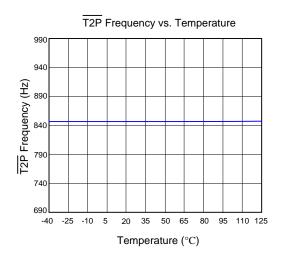


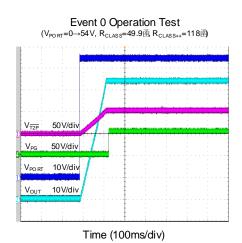


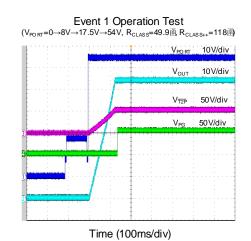






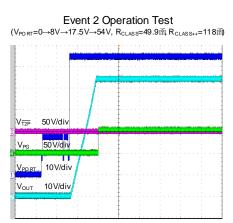




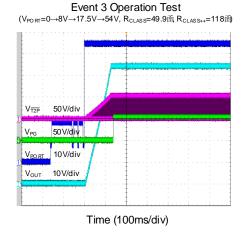


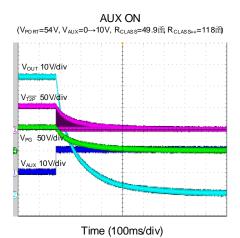


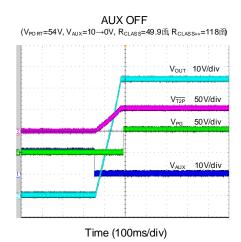














### **Application Information**

#### Overview

The IEEE 802.3af/at specification defines a process for safely powering a PD over a cable and removing power if a PD is disconnected. The process consist of three operational states: detection, classification, and operation.

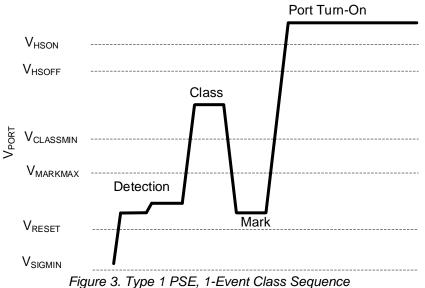
The SY28902B is designed to support higher power applications while maintaining backward compatibility with existing PSE systems. To eliminate expensive heat sinks, the SY28902B uses an external low R<sub>DS(ON)</sub> N-channel hot-swap MOSFET to increase end-to-end power transmission efficiency.

### **Modes of Operation**

#### **Detection Signature**

When a voltage in the range of 2.7V to 10.1V is applied to the PI, an incremental resistance of  $25k\Omega$  signals the Power Supply Equipment (PSE) that the PD can accept power. Figure 3 shows the detection voltages of PSE. The PSE calculates the signature resistance using a  $\Delta V/\Delta I$  measurement technique.

The SY28902B integrates a temperature-compensated, precision 24.4k signature resistor between the VPORT and GND pins. The PSE requests power to be applied if a valid PD is recognized. Typically, the SY28902B signature resistor is smaller than 25k to compensate for the additional series resistance on the line.

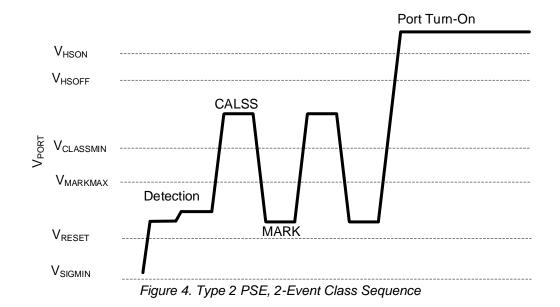


#### **Classification Signature and Mark**

The SY28902B may optionally provide a classification signature to the PSE, indicating the maximum power it will draw during operation. The IEEE specification defines this signature as a constant current draw when the PSE port voltage is in the V<sub>CLASS</sub> range (between 14.5V and 20.5V). If the PSE applies a classification probe voltage, the PSE returns the PD voltage to the mark voltage range before applying another classification probe voltage or powering up the PD.

An example of 1-Event classification is shown in Figure 3. In a 2-Event classification, a PSE probes for power classification twice, as shown in Figure 4. The SY28902B recognizes this and pulls the T2P pin down to signal to the load that Type 2 power is available. If a SY28902B senses a PSE of high-power mode, it will alternate between pulling T2P down and floating T2P at a rate of  $f_{T2P}$ .





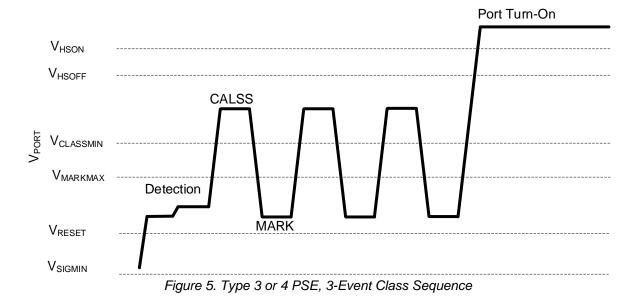




Table 1. Classification Codes, Power Levels, and Resistor Selection

PD REQUESTED	PD POWER	PD TYPES	NOMINAL CLASS	RESIST	OR (1%)
CLASS	AVAILABLE	PDTTPES	CURRENT	R <sub>CLS</sub>	R <sub>CLS++</sub>
0	13W	Type 1	2.5mA	1.00kΩ	Open
1	3.84W	Type 1	10.5mA	140Ω	Open
2	6.49W	Type 1	18.5mA	76.8Ω	Open
3	13W	Type 1	28mA	49.9Ω	Open
4	25.5W	Type 2	40mA	34.8Ω	Open
High-power Mode (38.7W or 5)	32.7W	High-power Mode	40mA/2.5mA	1.00kΩ	37.4Ω
High-power Mode (52.7W or 6)	52.7W	High-power Mode	40mA/10.5mA	140Ω	46.4Ω
High-power Mode (70W or 7)	70W	High-power Mode	40mA/18.5mA	76.8Ω	64.9Ω
High-power Mode (90W or 8)	90W	High-power Mode	40mA/28mA	49.9Ω	118Ω

#### **High-Power Mode**

The SY28902B allows higher power allocation while maintaining backward compatibility with existing PSE systems by extending the classification signaling of IEEE 802.3.

The PSEs supporting high-power modes present up to three classification events. As shown in Figure 5, a PSE of high-power mode probes for power classification three times in 3-event classification. The SY28902B recognizes this and alternates between pulling  $\overline{T2P}$  down and floating  $\overline{T2P}$  at a rate of  $f_{T2P}$  to signal the load that higher power is available.

#### **Signature Corrupt During Mark Event**

In this case, the SY28902B presents a resistance value <11k $\Omega$  to the port according to the requirements of the IEEE 802.3 specification during the mark event.

#### **Demotion and Denial in High-Power Mode**

IEEE 802.3 PSEs may demote PDs to a lower power state when the PD Requested Power exceeds the PSE available power. When two or fewer class/mark events are received, PD allocated power is at or below 25.5W, and the PSEs of high-power mode are considered equivalent to IEEE 802.3 PSEs.

**Table 2. PSE Allocated Power** 

PD REQUESTED	NUM	NUMBER OF PSE CLASS/MARK EVENTS				
CLASS	1	2	3			
0		13W				
1		3.84W				
2		6.49W				
3		13W				
4	13W	<b>13W</b> 25.5W				
High-power Mode	13W	25.5W	38.7W			
(38.7W or 5)	15**	25.511	36.7 VV			
High-power Mode	13W	25.5W	52.7W			
(52.7W or 6)	15**	25.511	32.7 VV			
High-power Mode	13W	25.5W	70W			
(70W or 7)	1344	25.5**	7000			
High-power Mode	13W	25.5W	90W			
(90W or 8)	1344	25.5	3000			

Note: Bold indicates the PD has been demoted.



#### Selection of Classification Resistors (Rcls and Rcls++)

Select the value R<sub>CLS</sub> and R<sub>CLS++</sub> resistors to configure the classification currents from Table 1 to the PD power classification. Connect each 1% resistor between the R<sub>CLASS++</sub> pins, and GND.

#### **Detection Signature Corrupt During Mark Event**

The SY28902B presents <11k $\Omega$  to the port according to the requirements of the IEEE 802.3 specification during the mark event.

#### Inrush and Power On

The PSE turns on the power to the PD once the PSE detects and classifies the PD. The SY28902B begins to source I<sub>GPU</sub> out of the HSGATE pin when the port voltage rises above the V<sub>HSON</sub> threshold. This current flows into an external capacitor, such as C<sub>GATE</sub> shown in Figure 8, which causes the gate of the external MOSFET to rise. The external N-channel MOSFET acts as a source follower and causes the voltage ramp on the output bulk capacitor C<sub>OUT</sub> to rise, thereby determining the inrush current (I<sub>INRUSH</sub>). A typical design target for I<sub>INRUSH</sub> is approximately 100mA. The value for C<sub>GATE</sub> can be calculated using the following equation:

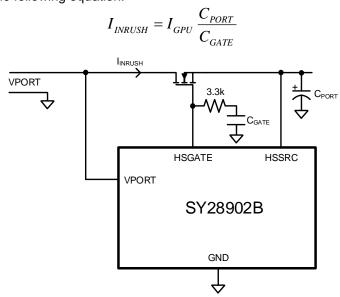


Figure 6. I<sub>INRUSH</sub> Configuration

The SY28902 internal charge pump enables the use of N-channel MOSETs due to their lower cost and R<sub>DS(ON)</sub>. Using a low R<sub>DS(ON)</sub> MOSFET maximizes power transmission efficiency, reduces power and heat dissipation, and simplifies thermal design.

#### **Power Good Indicator**

The PWRGD pin can be used to disable the downstream circuits until the external MOSFET is fully biased and inrush time is complete. The PWRGD pin remains low until HSGATE is charged to approximately 8V above HSSRC. The HSGATE pin remains high, and the PWRGD pin is in high-impedance until the port voltage falls below V<sub>HSOFF</sub>.

#### **Auxiliary Supply Override**

The SY28902B enters auxiliary power supply override mode if the AUX pin is held above  $V_{AUXT}$ . In this mode of operation, the signature resistor disconnects, HSGATE pulls down, classification is turned off, the PWRGD pin is high-impedance, and the  $\overline{T2P}$  pin indicates max available power.

The AUX pin allows for setting the auxiliary supply turn on and turn off voltage thresholds,  $V_{AUXON}$ , and  $V_{AUXOFF}$ , respectively. The auxiliary supply hysteresis voltage,  $V_{AUXHYS}$ , is generated with a current sink,  $I_{AUXH}$ , and is active only when the AUX pin voltage is less than  $V_{AUXT}$ . Use the following equations to set  $V_{AUXON}$  and  $V_{AUXOFF}$  via R1 and R2 in Figure 7. Note that an internal 6.7V Zener limits the voltage on the AUX pin.



A capacitor up to 1000pF may be placed between the AUX pin and GND to improve noise immunity.  $V_{AUXON}$  must be lower than  $V_{HSOFF}$ .

$$V_{AUXON} = \left(\frac{R_1}{R_2} + 1\right) V_{AUXT} + I_{AUXT} R_1$$

$$V_{AUXOFF} = V_{AUXON} - \left(\frac{R_1}{R_2} + 1\right) V_{AUX\_HY}$$

$$V_{AUXOFF} = V_{AUXON} - \left(\frac{R_1}{R_2} + 1\right) V_{AUX\_HY}$$

$$V_{AUXOFF} = V_{AUXON} - \left(\frac{R_1}{R_2} + 1\right) V_{AUX\_HY}$$

Figure 7. AUX Threshold and Hysteresis Calculation

#### **AUX Zener Limit**

If the AUX pin is driven above the internal Zener voltage threshold of 6.7V, the SY28902 will clamp the voltage to this level. For safe operation, the maximum current flowing into the AUX pin has to be lower than 1.4mA. Use a  $R_1$  value higher than the resistance value calculated using the following equation:

$$R_1 \ge \frac{V_{AUXON(MAX)} - 6.7V}{1.4mA}$$

### **T2P** Output

The  $\overline{12P}$  pin state is determined by the number of classification events, the RCLASS++ pin, and the AUX pin and also depends on the PSE allocated power. The SY28902 uses a 5-state encoding for the  $\overline{12P}$  output by changing the pin level and/or the duty cycle. Table 3 lists the  $\overline{12P}$  state based on the above input conditions:

Table 3. T2P Response to Determine PSE Allocated Power

AUX STATE	PD REQUESTED CLASS (RCLASS/ RCLASS++)	NUMBER OF CLASSIFICATION EVENTS	T2P WITH RESPECT TO GND	PSE ALLOCATED POWER
	0-4	N/A	Low-Z	AUX Power
AUXILIARY	5-8	N/A	50% Low-Z 50% HI-Z	AUX Power
PoE af/at	0-4	1	HI-Z	13W
POE al/at		≥ 2	Low-Z	25.5W
		1	HI-Z	13W
High-power Mode	5-8	2	Low-Z	25.5W
r light-power lylode	J-0	≥ 3	50% Low-Z 50% HI-Z	PD requested higher power

The AUX pin is the highest priority input. AUX is de-asserted to enter the PoE state and is asserted to enter the auxiliary power state. Based on PD requested class, the  $\overline{12P}$  pin indicates the highest available power in the auxiliary power state. The auxiliary power supply must be sized to provide at least the power required by the PD.

As shown in Table 1, the PD Requested Class is configured using the RCLASS and RCLASS++ pins. The RCLASS++ pin can be used to determine if the PD Class is 0-4 or high-power mode.

As shown in Table 2, the number of classification events determines the power allocated by the PSE.



#### **Thermal Shutdown Protection**

A PD must meet the IEEE 802.3 specification required to indefinitely withstand any applied voltage from 0V to 57V.

However, during the classification process, the power dissipation of the SY28902B may be as high as 1.5W. The SY28902B easily tolerates this during the maximum IEEE classification timing, but it can overheat if this condition persists for a long time. The SY28902B includes a thermal shutdown protection function to protect equipment under transient overload conditions. If the junction temperature exceeds the over-temperature threshold, the SY28902B pulls down HSGATE pin and disables classification.

### **External Interface and Component Selection**

#### **PoE Input Bridge**

A PD needs to perform polarity correction of its input voltage. There are several options for bridge rectifiers: ideal diodes, silicon diodes, and Schottky diodes. When using Schottky or silicon diode bridges, the voltage at the VPORT pin will be reduced due to the forward voltage across the diodes. The SY28902 is designed to tolerate these voltage drops.

Silicon diode bridges perform poorly, are unbalanced from wiring pair to pair, and consume up to 4% of the available power. In addition, thermal runaways can cause significant, non-compliant current unbalance between pair sets. Although using Schottky diodes can help reduce power loss and offer lower forward voltages, Schottky bridges may not be suitable for high-temperature PD applications, due to the increase of leakage currents at high temperature and a dependance of the leakage with voltage, as this can lead to an invalid detection signature. The increased leakage currents can also backfeed through the unpowered branch and the unused bridge, violating the IEEE 802.3 specifications.

### **Auxiliary Input Diode Bridge**

Some PDs require an auxiliary power source to receive AC or DC power. A diode bridge is typically required to handle the polarity correction and voltage rectification.

#### **Input Capacitor**

Add a 0.1µF capacitor between VPORT and GND to meet the input impedance requirement of IEEE 802.3 and appropriately bypass the SY28902B.

#### **Transient Voltage Suppressor**

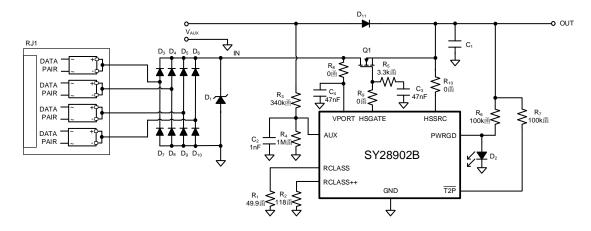
The SY28902 is specified to withstand an absolute maximum input voltage of 100V, and it can tolerate brief over-voltage events due to Ethernet cable surges. To protect the SY28902 from an over-voltage event, a unidirectional transient voltage suppressor (TVS), such as an SMAJ60A, should be used between the VPORT and GND pins.

#### **Exposed Pad**

The SY28902B DFN package has an exposed pad internally electrically connected to the GND. The exposed pad may only be connected to GND on the printed circuit board.



# **Application Schematic**



#### **BOM List**

Designator	Description	Part Number	Manufacturer
C <sub>1</sub>	/	/	/
$C_2$	1nF/50V, 0603	GRM1885C1H102GA01D	Murata
C <sub>3</sub>	47nF/100V, 0805	GRM21BR72A4473KA01L	Murata
C <sub>4</sub>	47nF/100V, 0805	GRM21BR72A4473KA01L	Murata
R <sub>1</sub>	49.9Ω, 0603	RC0603FR-0749R9L	YAGEO
R <sub>2</sub>	118Ω, 0603	RC0603FR-07118RL	YAGEO
R₃	340kΩ, 0603	RC0603FR-07340KL	YAGEO
R <sub>4</sub>	1ΜΩ, 0603	RC0603FR-071ML	YAGEO
R <sub>5</sub>	3.3kΩ, 0603	RC0603FR-073K3L	YAGEO
R <sub>6</sub>	100kΩ, 0603	RC0603FR-07100KL	YAGEO
R <sub>7</sub>	100kΩ, 0603	RC0603FR-07100KL	YAGEO
R <sub>8</sub> , R <sub>9</sub> ,R <sub>10</sub>	0	/	/
$D_1$	TVS/60V, SMA	SMAJ60A	Littelfuse
$D_2$	LED	/	/
D <sub>3</sub> -D <sub>11</sub>	Schottky/100V	SS3100	TOSHIBA
RJ1	J1 RJ45 RJ45-B-1*1		BOOMELE
$Q_1$	NMOS/100V	FDMS86150	Fairchild

#### **Layout Considerations**

Place resistors  $R_{CLS}$  and  $R_{CLS++}$  close to the SY28902B to avoid excessive parasitic capacitance on the RCLASS and RCLASS++ pins.

It is strictly required for maximum protection to place the  $0.1\mu F$  input capacitor,  $C_{PD}$ , and transient voltage suppressor as close to the SY28902B as possible.



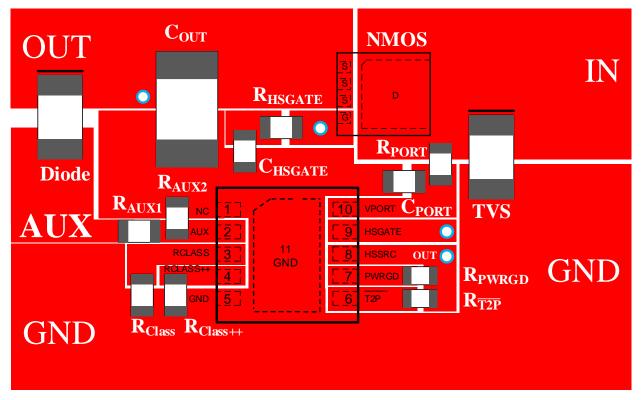
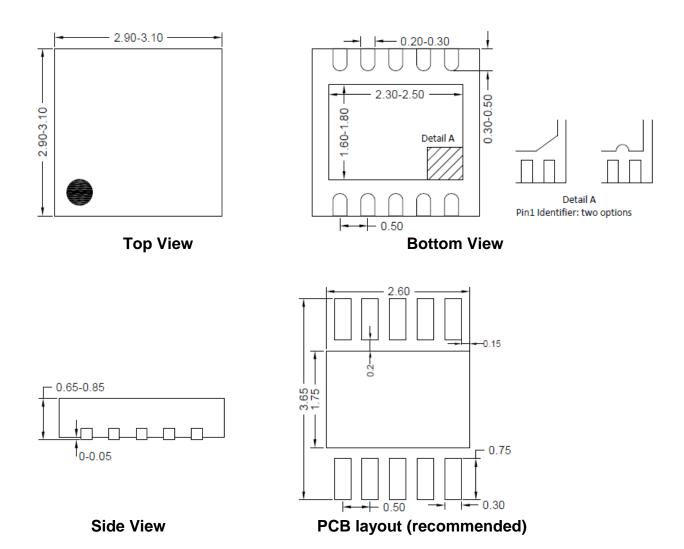


Figure 8. PCB Layout Suggestion



# **DFN3×3-10 Package Outline**

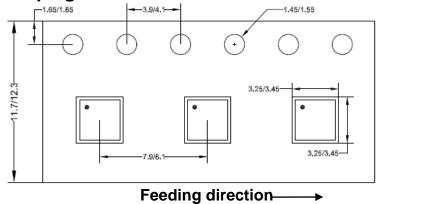


Notes: All dimensions are in millimeters and exclude mold flash and metal burr.

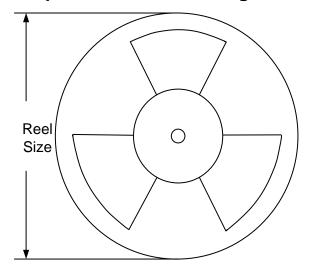


# **Taping & Reel Specification**

# **DFN3×3-10 Taping Orientation**



# **Carrier Tape & Reel Specification for Packages**



Package types	Tape width (mm)	Pocket pitch(mm)	Reel size (Inch)	Trailer length(mm)	Leader length (mm)	Qty per reel
DFN3×3	12	8	13"	400	400	5000

Others: NA





# **Revision History**

Date	Revision	Change
Oct.19, 2023	Revision 1.0	Language improvements for clarity.
Jan.10, 2022	Revision 0.9	Initial Release

The revision history provided is for informational purposes only and is believed to be accurate; however, it is not warranted. Please make sure that you have the latest revision.



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